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(54) Title: METHODS OF FORMING A PLURALITY OF CAPACITORS

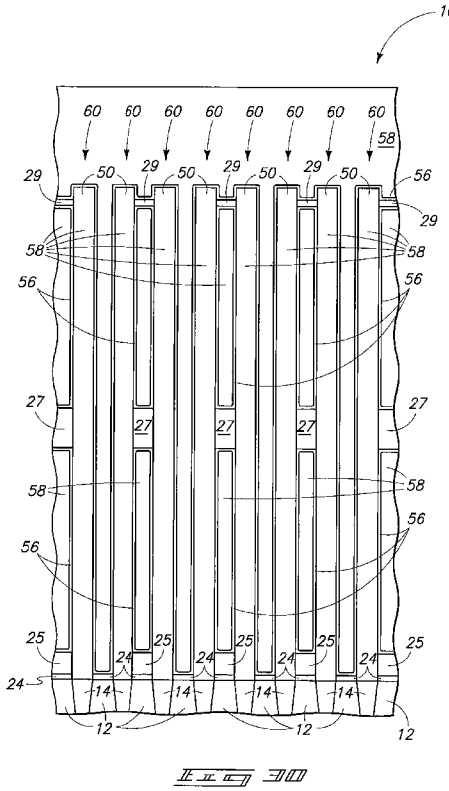


Fig. 3D

(57) Abstract: A method of forming a plurality of capacitors includes forming a plurality of individual capacitor electrodes using two masking steps. An earlier of the two masking steps is used to form an array of first openings over a plurality of storage node contacts. A later of the two masking steps is used to form an array of second openings received partially over and partially offset from the array of first openings. Overlapping portions of the first and second openings are received over the storage node contacts. After both of the two masking steps, conductive material of the individual capacitor electrodes is deposited into the overlapping portions of each of the first and second openings. The individual capacitor electrodes are incorporated into a plurality of capacitors. Other aspects and implementations are contemplated.

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